

**IN THE CLAIMS:**

This listing of claims will replace all prior versions, and listings, of claims in the application:

Claims 3-6 have been amended as follows:

**Listing of Claims:**

Claim 1 (original): A dry etching method characterized in that a resist film formed on a substrate is irradiated with radiation having a wavelength of not more than 195 nm to form a resist pattern having a minimum line width of not more than 200 nm, and the substrate having the resist pattern formed thereon is subjected to dry etching using a fluorine-containing compound having 4 to 6 carbon atoms and at least one unsaturated bond as an etching gas.

Claim 2 (original): The dry etching method according to claim 1, wherein the resist film is formed from a high molecular weight compound containing 0% to 10% by weight of repeating units having an aromatic ring structure.

Claim 3 (currently amended): The dry etching method according to claim 1 [[or 2]], wherein the fluorine-containing compound having 4 to 6 carbon atoms and at least one unsaturated bond is selected from perfluoro-2-butyne and perfluoro-2-pentyne.

Claim 4 (currently amended): The dry etching method according to claim 1 [[or 2]], wherein the fluorine-containing compound having 4 to 6 carbon atoms is perfluoro-2-pentyne.

Claim 5 (currently amended): The dry etching method according to claim 1 [[or 2]], wherein the fluorine-containing compound having 4 to 6 carbon atoms and at least one unsaturated bond is at least one kind of flouropentene selected from 1,1,1,2,4,4,5,5,5-nonafluoro-2-pentene,

1,1,1,3,4,4,5-nonafluoro-2-pentene and perfluoro-2-pentene.

Claim 6 (currently amended): The dry etching method according to ~~any one of claims 1 to 5~~ claim 1, wherein the dry etching is carried out under irradiation with plasma having a plasma density of at least  $10^{10}$  ions/cm<sup>3</sup>.

Claim 7 (original): A dry etching gas comprised of a fluorine-containing compound having 4 to 6 carbon atoms and at least one unsaturated bond, and used for dry etching for a resist film forming a resist pattern having a minimum line width of not more than 200 nm at irradiation with radiation having a wavelength of not more than 195 nm.

Claim 8 (original): The dry etching gas according to claim 7, wherein the fluorine-containing compound having 4 to 6 carbon atoms and at least one unsaturated bond is selected from perfuloro-2-butyne and perfuloro-2-pentyne.

Claim 9 (original): The dry etching gas according to claim 7, wherein the fluorine-containing compound having 4 to 6 carbon atoms and at least one unsaturated bond is perfuloro-2-pentyne.

Claim 10 (original): The dry etching gas according to claim 7, wherein the fluorine-containing compound having 4 to 6 carbon atoms and at least one unsaturated bond is at least one kind of fluoropentene selected from 1,1,1,2,4,4,5,5,5-nonafluoro-2-pentene, 1,1,1,3,4,4,5-nonafluoro-2-pentene and perfluoro-2-pentene.

Claim 11 (original): A process for producing perfluoro-2-pentyne characterized in that a 1,1,1-trihalo-2,2,2-trifluoroethane is allowed to react with pentafluoropropionaldehyde to give a 2-halo-1,1,1,4,4,5,5,5-octafluoro-2-pentene, and the thus-produced 2-halo-1,1,1,4,4,5,5,5-octafluoro-2-pentene is dehydrohalogenated.

**Claim 12 (original):** The process for producing perfluoro-2-pentyne according to claim 11, wherein the 1,1,1-trihalo-2,2,2-trifluoroethane is 1,1,1-trichloro-2-2-2-trifluoroethane.